

### STTH4R06DEE

### Turbo 2 ultrafast recovery diode

Datasheet - production data

#### **Features**

- Very low switching losses
- High frequency and high pulse current operation
- Low thermal resistance
- High junction temperature
- ECOPACK<sup>®</sup>2 compliant component

### **Description**

The STTH4R06 series uses ST's new 600 V planar Pt doping technology. The STTH4R06 is specially suited for switching mode base drive and transistor circuits.

Packaged in PowerFLAT™, this device is intended for use in low profile applications.

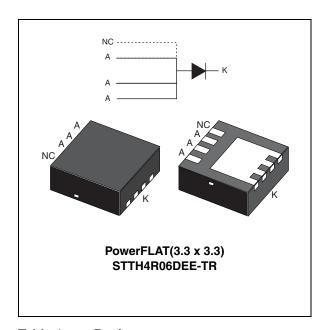


Table 1. Device summary

Symbol	Value
I <sub>F(AV)</sub>	4 A
V <sub>RRM</sub>	600 V
T <sub>j</sub> (max)	150 °C
V <sub>F</sub> (typ)	1.0 V
T <sub>RR</sub> (typ)	30 ns

TM: PowerFLAT is a trademark of STMicroelectronics

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### 1 Characteristics

Table 2. Absolute ratings (limiting values  $T_{amb} = 25$  °C unless otherwise specified)

Symbol	Parameter	Value	Unit	
V <sub>RRM</sub>	Repetitive peak reverse voltage	600	V	
I <sub>F(RMS)</sub>	Forward rms current		15	Α
I <sub>F(AV)</sub>	Average forward current	4	Α	
I <sub>FSM</sub>	Surge non repetitive forward current	60	Α	
T <sub>stg</sub>	Storage temperature range	-65 to +150	°C	
Tj	Maximum operating junction tempera	150	°C	

Table 3. Thermal resistance

Symbol	Parameter	Value	Unit
R <sub>th(j-c)</sub>	Junction to case	4.5	°C/W
R <sub>th(j-a)</sub>	Junction to ambient on printed circuit board (with recommended footprint, copper thickness = 35 µm)	250	°C/W

Table 4. Static electrical characteristics

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
I <sub>R</sub> <sup>(1)</sup>	Reverse leakage	T <sub>j</sub> = 25 °C	V <sub>R</sub> = V <sub>RRM</sub>	ı		3	μΑ
'R'	current	T <sub>j</sub> = 125 °C	VR - VRRM	ı	3	30	μΑ
V <sub>F</sub> <sup>(2)</sup>	Forward voltage drop	T <sub>j</sub> = 25 °C	I <sub>F</sub> = 4A		1.30	1.70	V
VF.	Torward voilage drop	T <sub>j</sub> = 150 °C		-	1.0	1.25	V

<sup>1.</sup> Pulse test:  $t_p = 5 \text{ ms}, \delta < 2\%$ 

To evaluate the conduction losses use the following equation:

$$P = 1 x I_{F(AV)} + 0.062 x I_{F}^{2}_{(RMS)}$$

 Table 5.
 Dynamic electrical characteristics

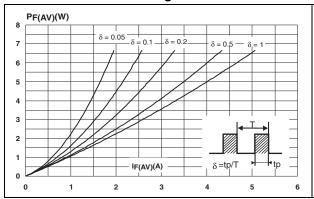
Symbol	Parameter	Test conditions			Тур.	Max.	Unit
I <sub>RM</sub>	Reverse recovery current	T <sub>i</sub> = 125 °C	$I_f = 125  ^{\circ}\text{C}$ $I_F = 4  \text{A},  V_R = 400  \text{V},$ $I_F = 4  \text{A},  V_R = 400  \text{V},$ $I_F = 4  \text{A},  V_R = 400  \text{A}$		5.5	7.5	Α
S <sub>factor</sub>	Softness factor	•			2		
+	Reverse recovery time	T <sub>i</sub> = 25 °C	$I_F = 1A$ , $V_R = 30 V$ , $dI_F/dt = -50 A/\mu s$		35	50	ns
t <sub>rr</sub>	Theverse recovery time	1; - 25 0	$I_F = 1A$ , $V_R = 30$ V, $dI_F/dt = -100$ A/ $\mu$ s		30	40	113
t <sub>fr</sub>	Forward recovery time	$T_j = 25  ^{\circ}\text{C}$ $I_F = 4  \text{A},  V_{FR} = 2  \text{V}$				100	ns
V <sub>FP</sub>	Forward recovery voltage		$dl_F/dt = 100 \text{ A/}\mu\text{s}$		3.5	5	V

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<sup>2.</sup> Pulse test:  $t_p = 380 \mu s$ ,  $\delta < 2\%$ 

STTH4R06DEE Characteristics

Figure 1. Average forward power dissipation Figure 2. Forward voltage drop versus versus average forward current forward current



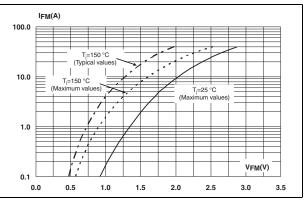
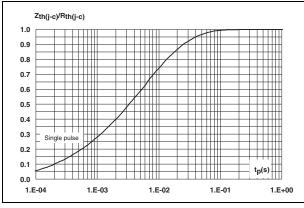


Figure 3. Relative variation of thermal impedance junction to case versus pulse duration

Figure 4. Peak reverse recovery current versus dl<sub>F</sub>/dt (typical values)



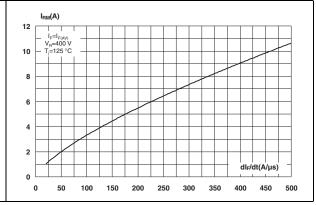
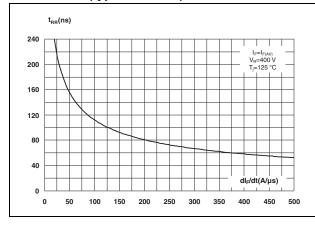
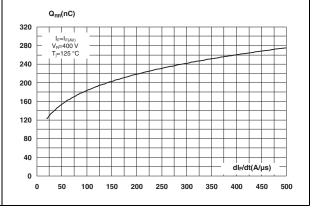


Figure 5. Reverse recovery time versus  $dl_F/dt$  Figure 6. (typical values)

Reverse recovery charges versus dl<sub>F</sub>/dt (typical values)





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Figure 7. Reverse recovery softness factor versus dl<sub>E</sub>/dt (typical values)

Figure 8. Relative variation of dynamic parameters versus junction temperature

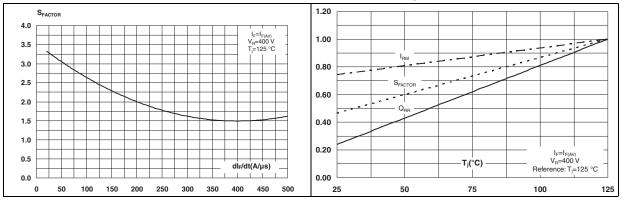


Figure 9. Transient peak forward voltage versus dl<sub>F</sub>/dt (typical values)

Figure 10. Forward recovery time versus dl<sub>F</sub>/dt (typical values)

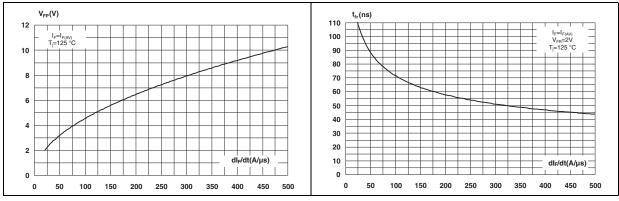
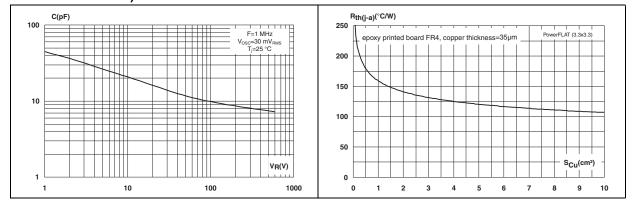


Figure 11. Junction capacitance versus reverse voltage applied (typical values)

Figure 12. Thermal resistance junction to ambient versus copper surface under tab



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### 2 Package information

- Epoxy meets UL94,V0
- Lead-free package

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: <a href="https://www.st.com">www.st.com</a>. ECOPACK<sup>®</sup> is an ST trademark.

Figure 13. PowerFLAT (3.3 x 3.3) dimensions (definitions)

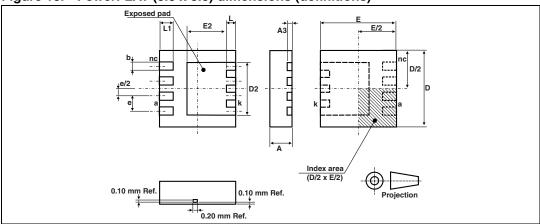
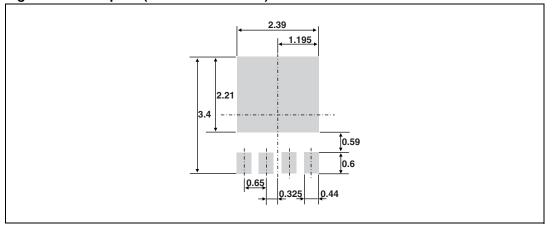


Table 6. PowerFLAT (3.3 x 3.3) dimensions (values)

	Dimensions					
Ref.	Millimeters					
	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	0.95		1.0	0.037		0.039
A3		0.2			0.008	
b	0.29	0.34	0.39	0.011	0.013	0.015
D	3.20	3.30	3.40	0.126	0.130	0.134
D2	2.24	2.29	2.34	0.088	0.090	0.092
E	3.20	3.30	3.40	0.126	0.130	0.134
E2	1.66	1.71	1.76	0.065	0.067	0.069
е		0.65			0.026	
L		0.40			0.016	
L1	0.45	0.50	0.55	0.018	0.20	0.22

Package information STTH4R06DEE

Figure 14. Footprint (dimensions in mm)



# 3 Ordering information

Table 7. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STTH4R06DEE-TR	TH4R06	PowerFLAT (3.3 x 3.3)	34 mg	3000	Tape and reel 13" reel

## 4 Revision history

Table 8. Document revision history

Date	Revision	Changes
11-Sep-2012	1	First issue.

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